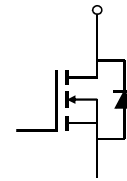


100V 2.8m N-Ch Power MOSFET

Features

Product Summary

Parameter	Value	Unit
V_{DS}	100	V
$V_{GS(th)}_{Typ}$	2.7	V
I_D (@ $V_{GS} = 10V$) ⁽¹⁾	196	A
$R_{DS(ON)}_{Typ}$ (@ $V_{GS} = 10V$)	2.8	m



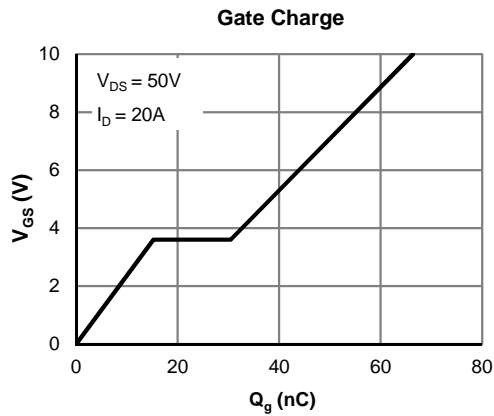
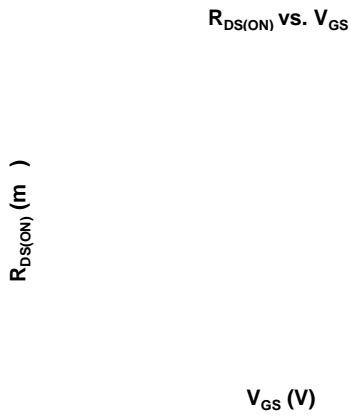
Rev. 1.1

Ordering Information

Device	Package	# of Pins	Marking	MSL	T_J (°C)	Media	Quantity (pcs)
JMSH1003AE7Q-13	TO-263-7L	7	SH1003AQ	1	-55 to 175	13-inch Reel	800

Absolute Maximum Ratings (@ $T_A = 25^\circ C$ unless otherwise specified)

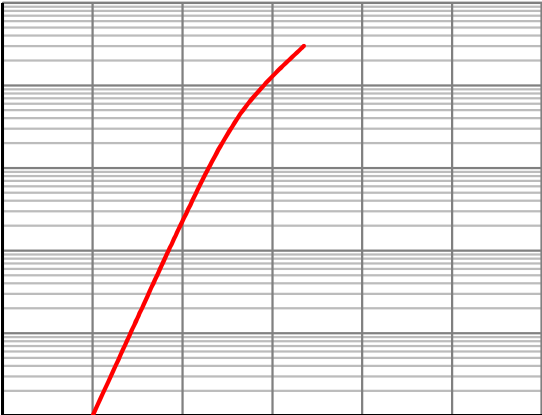
Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DS}	100	V
Gate-to-Source Voltage	V_{GS}	± 20	V
			A
	I_{DM}		A
Avalanche Current ⁽³⁾	I_{AS}	52	A
Avalanche Energy ⁽³⁾	E_{AS}	406	mJ
Power Dissipation ⁽⁴⁾	P_D	283	W
		142	W
Junction & Storage Temperature Range	T_J, T_{STG}	-55 to 175	°C



	Symbol	Min.	Typ.	Max.	Unit
Gate Threshold Voltage	$V_{(BR)DSS}$	100			V
				1.0	
				5.0	
	I_{GSS}			± 100	nA
	$V_{GS(th)}$	2.0	2.7	4.0	V
	$R_{DS(on)}$		2.8	3.5	m
	g_{FS}		85		S
	V_{SD}		0.71	1.0	V
	I_S			283	A
	C_{iss}		4398		pF
	C_{oss}		1361		pF
	C_{rss}		8.5		pF
	R_g		2.5		
	Q_g		66		nC
	Q_g		44		nC
	Q_{gs}		15.2		nC
	Q_{gd}		15.2		nC
	$t_{D(on)}$		17.2		ns
	t				

$V_{DS} = 80V, V_{GS} = 0V$
 $T_J = 55^\circ C$

Typical Electrical & Thermal Characteristics



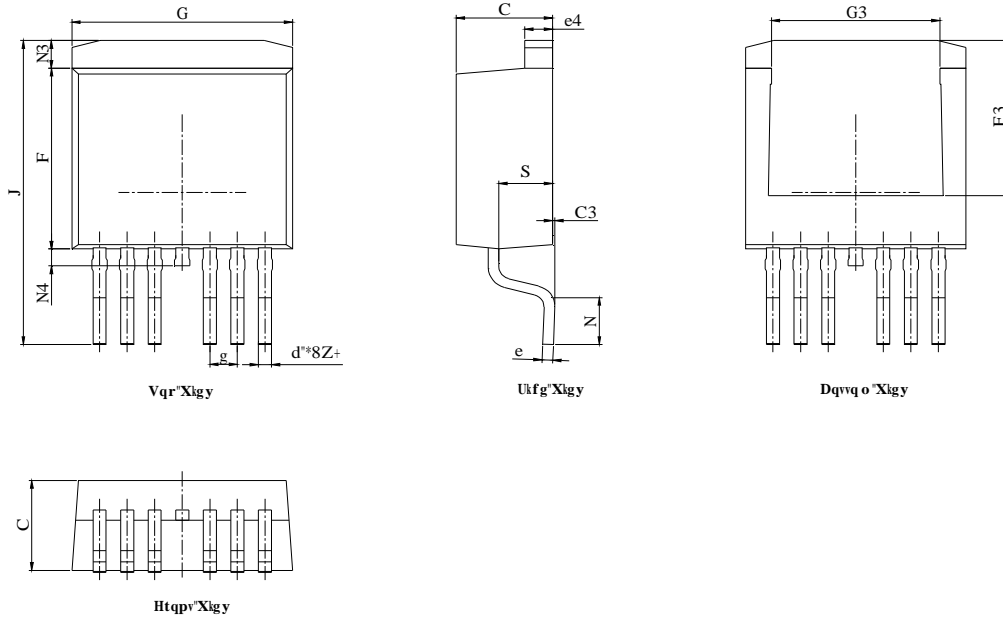


Typical Electrical & Thermal Characteristics



TO-263-7L Package Information

Package Outline



FKO	OINNIOGVGT		
	OXP	PQO	OCZ
C	6046	6066	6086
C3	2022	2032	2047
d	2072	2082	2092
e	2062	2072	2082
e4	3037	3049	3062
F	:0:4	:0:4	:024
F3	9087TGH		
G	:0:8	32038	32058
G3	80:2	90:2	:022
g	3049DUE		
J	36083	37022	370:
N	309:	4054	40:2
N3		3058TGH	
N4		3042TGH	
N5		2047DUE	
S	4052	406:	4092

Tgeq o o gpfgf"Uqifgtpi"Hqqvrtkp

